

**CMXDM7002A****SURFACE MOUNT SILICON  
DUAL N-CHANNEL  
ENHANCEMENT-MODE  
MOSFET****SOT-26 CASE**[www.centrasemi.com](http://www.centrasemi.com)**DESCRIPTION:**

The CENTRAL SEMICONDUCTOR CMXDM7002A is special dual version of the 2N7002 enhancement-mode N-Channel MOSFET manufactured by the N-Channel DMOS Process, and designed for high speed pulsed amplifier and driver applications. This special dual transistor device offers low  $r_{DS(ON)}$  and low  $V_{DS(ON)}$ .

**MARKING CODE: X02A****MAXIMUM RATINGS:** ( $T_A=25^\circ\text{C}$ )

Drain-Source Voltage
Drain-Gate Voltage
Gate-Source Voltage
Continuous Drain Current
Continuous Source Current (Body Diode)
Maximum Pulsed Drain Current
Maximum Pulsed Source Current
Power Dissipation
Operating and Storage Junction Temperature
Thermal Resistance

**SYMBOL**

$V_{DS}$	60
$V_{DG}$	60
$V_{GS}$	40
$I_D$	280
$I_S$	280
$I_{DM}$	1.5
$I_{SM}$	1.5
$P_D$	350
$T_J, T_{stg}$	-65 to +150
$\Theta_{JA}$	357

**UNITS**

V
V
V
mA
mA
A
A
mW
$^\circ\text{C}$
$^\circ\text{C/W}$

**ELECTRICAL CHARACTERISTICS PER TRANSISTOR:** ( $T_A=25^\circ\text{C}$  unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
$I_{GSSF}, I_{GSSR}$	$V_{GS}=20\text{V}, V_{DS}=0$		100	nA
$I_{DSS}$	$V_{DS}=60\text{V}, V_{GS}=0$		1.0	$\mu\text{A}$
$I_{DSS}$	$V_{DS}=60\text{V}, V_{GS}=0, T_J=125^\circ\text{C}$		500	$\mu\text{A}$
$I_{D(ON)}$	$V_{GS}=10\text{V}, V_{DS}=10\text{V}$	500		mA
$BV_{DSS}$	$V_{GS}=0, I_D=10\mu\text{A}$	60		V
$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu\text{A}$	1.0	2.5	V
$V_{DS(ON)}$	$V_{GS}=10\text{V}, I_D=500\text{mA}$		1.0	V
$V_{DS(ON)}$	$V_{GS}=5.0\text{V}, I_D=50\text{mA}$		0.15	V
$V_{SD}$	$V_{GS}=0, I_S=400\text{mA}$		1.2	V
$r_{DS(ON)}$	$V_{GS}=10\text{V}, I_D=500\text{mA}$		2.0	$\Omega$
$r_{DS(ON)}$	$V_{GS}=10\text{V}, I_D=500\text{mA}, T_J=125^\circ\text{C}$		3.5	$\Omega$
$r_{DS(ON)}$	$V_{GS}=5.0\text{V}, I_D=50\text{mA}$		3.0	$\Omega$
$r_{DS(ON)}$	$V_{GS}=5.0\text{V}, I_D=50\text{mA}, T_J=125^\circ\text{C}$		5.0	$\Omega$
gFS	$V_{DS}=10\text{V}, I_D=200\text{mA}$	80		mS
$C_{rss}$	$V_{DS}=25\text{V}, V_{GS}=0, f=1.0\text{MHz}$		5.0	pF
$C_{iss}$	$V_{DS}=25\text{V}, V_{GS}=0, f=1.0\text{MHz}$		50	pF
$C_{oss}$	$V_{DS}=25\text{V}, V_{GS}=0, f=1.0\text{MHz}$		25	pF

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CMXDM7002A

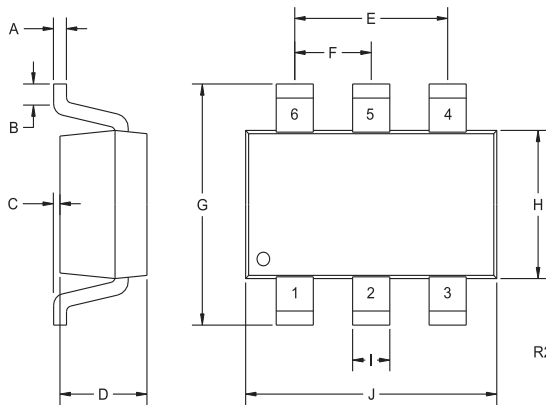
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**ELECTRICAL CHARACTERISTICS PER TRANSISTOR - Continued:** ( $T_A=25^{\circ}\text{C}$  unless otherwise noted)

SYMBOL	TEST CONDITIONS	TYP	MAX	UNITS
$Q_{g(\text{tot})}$	$V_{DS}=30\text{V}$ , $V_{GS}=4.5\text{V}$ , $I_D=100\text{mA}$	0.592		nC
$Q_{gs}$	$V_{DS}=30\text{V}$ , $V_{GS}=4.5\text{V}$ , $I_D=100\text{mA}$	0.196		nC
$Q_{gd}$	$V_{DS}=30\text{V}$ , $V_{GS}=4.5\text{V}$ , $I_D=100\text{mA}$	0.148		nC
$t_{\text{on}}$ , $t_{\text{off}}$	$V_{DD}=30\text{V}$ , $V_{GS}=10\text{V}$ , $I_D=200\text{mA}$ , $R_G=25\Omega$ , $R_L=150\Omega$		20	ns

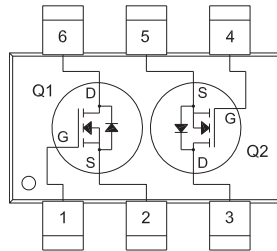
**SOT-26 CASE - MECHANICAL OUTLINE**



DIMENSIONS				
SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.004	0.007	0.11	0.19
B	0.016	-	0.40	-
C	-	0.004	-	0.10
D	0.039	0.047	1.00	1.20
E	0.074	0.075	1.88	1.92
F	0.037	0.038	0.93	0.97
G	0.102	0.118	2.60	3.00
H	0.059	0.067	1.50	1.70
I	0.016		0.41	
J	0.110	0.118	2.80	3.00

SOT-26 (REV: R2)

**PIN CONFIGURATION**



**LEAD CODE:**

- 1) Gate Q1
- 2) Source Q1
- 3) Drain Q2
- 4) Gate Q2
- 5) Source Q2
- 6) Drain Q1

**MARKING CODE: X02A**

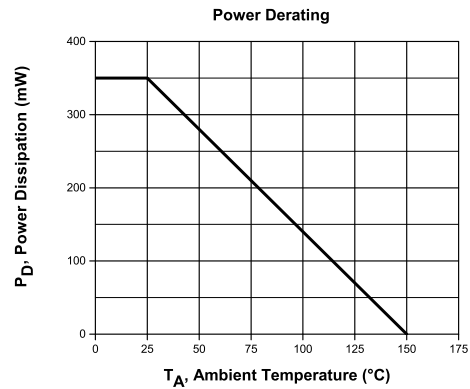
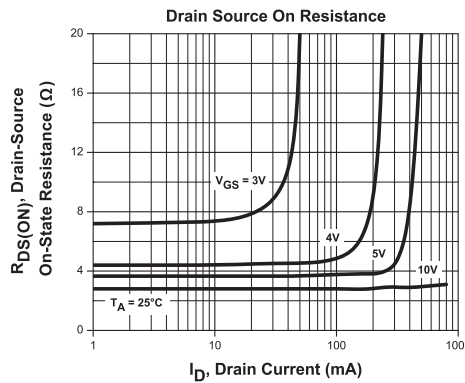
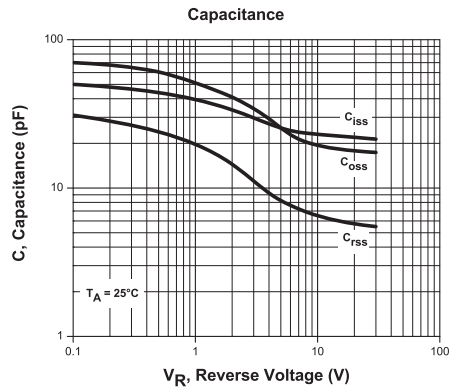
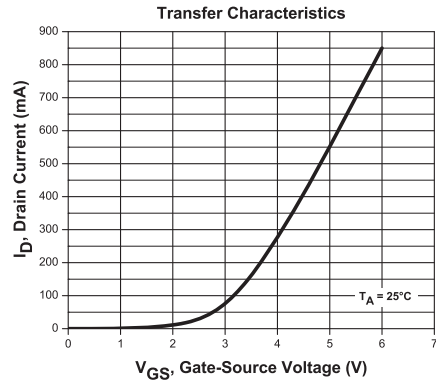
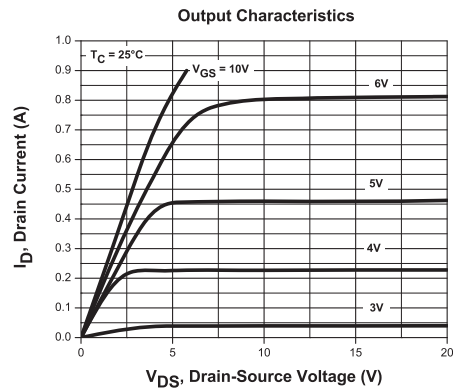
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## TYPICAL ELECTRICAL CHARACTERISTICS



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## OUTSTANDING SUPPORT AND SUPERIOR SERVICES



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### PRODUCT SUPPORT

Central's operations team provides the highest level of support to insure product is delivered on-time.

- Supply management (Customer portals)
- Inventory bonding
- Consolidated shipping options
- Custom bar coding for shipments
- Custom product packing

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### DESIGNER SUPPORT/SERVICES

Central's applications engineering team is ready to discuss your design challenges. Just ask.

- Free quick ship samples (2<sup>nd</sup> day air)
- Online technical data and parametric search
- SPICE models
- Custom electrical curves
- Environmental regulation compliance
- Customer specific screening
- Up-screening capabilities
- Special wafer diffusions
- PbSn plating options
- Package details
- Application notes
- Application and design sample kits
- Custom product and package development

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### REQUESTING PRODUCT PLATING

1. If requesting Tin/Lead plated devices, add the suffix " TIN/LEAD" to the part number when ordering (example: 2N2222A TIN/LEAD).
2. If requesting Lead (Pb) Free plated devices, add the suffix " PBFREE" to the part number when ordering (example: 2N2222A PBFREE).

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### CONTACT US

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